

Application No.: 10/616,095

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## AMENDMENTS

### In the claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (currently amended): A semiconductor device, comprising:

a light-receiving element having a light-receiving face formed on a main surface of a semiconductor substrate;

an antireflection coating formed so as to cover the light-receiving face of said light-receiving element, and formed by a prescribed layer for preventing reflection of incident light;

a protection film formed on said antireflection coating and protecting said antireflection coating; and

a mold material formed on said semiconductor substrate so as to directly cover said protection film,

wherein

said protection film has an index of refraction different from that of said mold material by at most 0.3; and

said protection film includes a polyimide-based resin.

Claim 2 (cancelled)

Claim 3 (original): The semiconductor device according to claim 1, wherein said protection film includes a silicon oxide film.

Claim 4 (cancelled)

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Claim 5 (original): The semiconductor device according to claim 1, further comprising a signal processing circuit portion for processing a prescribed signal, formed in a region of said semiconductor substrate different from a region where said light-receiving element is formed.

Claim 6 (currently amended): The semiconductor device according to claim 5, further comprising a first insulating film formed so as to cover said signal processing circuit portion, wherein

said protection film includes a film formed ~~[[with]]~~ in a same layer identical to in which said first insulating film is formed.

Claim 7 (currently amended): The semiconductor device according to claim 6, further comprising a first interconnection formed on said semiconductor substrate with a second insulating film interposed, wherein

said protection film includes a film formed ~~[[with]]~~ in a same layer identical to in which said second insulating film is formed.

Claim 8 (currently amended): The semiconductor device according to claim 7, further comprising a third insulating film formed so as to cover said first interconnection, wherein

said protection film includes a film formed ~~[[with]]~~ in a same layer identical to in which said third insulating film is formed.

Claim 9 (currently amended): The semiconductor device according to claim 8, further comprising a second interconnection formed on said third insulating film, and a fourth insulating film formed so as to cover said second interconnection, wherein

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said protection film includes a film formed ~~[[with]]~~ in a same layer identical to in which said fourth insulating film is formed.

Claim 10 (original): An optical device comprising a semiconductor device according to claim 1.

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